L Number	Hits	Search Text	DB	Time stamp
1 .	21	(("4292093") or ("4942058") or ("5024968") or ("5352291") or	USPAT;	2003/01/07 15:3
2		("5372836") or ("5424244") or ("5529630") or ("5593497") or	US-PGPUB;	1
		("5843225") or ("5842833")).PN.	EPO; JPO;	
			DERWENT;	!
	2	("E40E904") DN	IBM_TDB USPAT:	2002/04/07 45:20
2	2	("5405804").PN.	US-PGPUB;	2003/01/07 15:3
!				1
			EPO; JPO; DERWENT;	
			IBM_TDB	•
_ 1	2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795)	USPAT;	2003/01/07 11:1
Ì	20.0	or (438/909) or (438/for.200) or (438/for.269) or (438/for.334)	US-PGPUB;	2000/01/01 11:10
		or (117/8) or (117/9) or (117/10)).CCLS.	EPO; JPO;	
			DERWENT:	
			IBM TDB	
.	2937	laser with crystallization	USPAT:	2003/01/06 10:0
			US-PGPUB;	
ì		\ 1	EPO; JPO;	
1			DERWENT;	i
:			IBM_TDB	•
i	1421	(laser with crystallization) and laser with anneal\$3	USPAT;	2003/01/07 11:1
i			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	Í
			IBM_TDB	1
	1379	((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 10:5
		(silicon semiconductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	96	(//least with appetallization) and least with appeal(2) and	IBM_TDB	2003/01/03 11:0
i	90	(((laser with crystallization) and laser with anneal\$3) and (silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))	USPAT; US-PGPUB;	2003/01/03 11.0
		(sincorr semiconductor)) and (preneatos (pre adj neatos))	EPO; JPO;	
			DERWENT:	
			IBM TDB	1
-	52	(((((laser with crystallization) and laser with anneal\$3) and	USPAT:	2003/01/03 14:3
1	52	(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and	US-PGPUB:	2000.01100
1	j	clean\$4	EPO; JPO;	
1			DERWENT:	1
İ			IBM TDB	İ
i	5	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 11:3
1		(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and	US-PGPUB;	i
,		clean\$4) and @ad<=19951025	EPO; JPO;	1
-			DERWENT;	
			IBM_TDB	
-	2	("6348369").PN.	USPAT;	2003/01/03 11:3
			US-PGPUB;	
			EPO; JPO;	
	ĺ		DERWENT;	
	_ [IBM_TDB	
	3	("4180618" "4851363" "5064779").PN.	USPAT	2003/01/03 13:3
1	25	4180618.URPN.	USPAT	2003/01/03 13:3
1	6	5344796.URPN.	USPAT	2003/01/03 13:5
(9	("3998980" "4222814" "5242707" "5337207" "5344796"	USPAT	2003/01/03 13:5
1	_	"5434102" "5587343" "5757061" "5834803").PN.	LICDAT	2002/04/02 44:0
ĺ	3	("4180618" "4851363" "5064779").PN.	USPAT	2003/01/03 14:0
Ì	25	4180618.URPN.	USPAT	2003/01/03 14:0
1	6	("4019169" "4180618" "4643950" "4732801" "4795679"	USPAT	2003/01/03 14:1
1	40	"4847157").PN.	LICDAT	2002/04/02 44:4
ı	16	5108843.URPN.	USPAT	2003/01/03 14:1
ł		((((laser with crystallization) and laser with anneal\$3) and	USPAT;	, 2003/01/03 14:3
	52	(cilican semiconductor)) and (probable) (pro adi hootes))) and	HIS DODIES	
	J2 ;	(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and clean\$4	US-PGPUB;	
	J2 ;	(silicon semiconductor)) and (preheat\$3 (pre adj heat\$3))) and clean\$4	US-PGPUB; EPO; JPO; DERWENT;	

	334	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:16
		(silicon semiconductor)) and clean\$4)	US-PGPUB;	
			EPO; JPO;	<u> </u>
	1	 	DERWENT;	
	ł		IBM_TDB	1
-	249	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 14:43
		(silicon semiconductor)) and clean\$4)) and oxygen and	US-PGPUB;	•
	ł	nitrogen	EPO; JPO;	
	I		DERWENT;	
	1		IBM TDB	i .
_	264	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 14:44
	201	(silicon semiconductor)) and clean\$4)) and (oxygen "o.sub.2")	US-PGPUB;	2500,01,00
	•	and (nitrogen "n.sub.2")	EPO; JPO;	
	İ	and (minogen misable)	DERWENT;	1
	}		IBM TDB	<u> </u>
	37	((((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 14:44
-	31			1
		(silicon semiconductor)) and clean\$4)) and (oxygen "o.sub.2")	US-PGPUB;	
	1	and (nitrogen "n.sub.2")) and @ad<=19951025	EPO; JPO;	
			DERWENT;	
		/////	IBM_TDB	2002/04/02 45:47
-	52	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:17
	!	(silicon semiconductor)) and clean\$4)) and (preheat\$3 (pre adj	US-PGPUB;	•
		heat\$3))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:18
		(silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre	US-PGPUB;	
		adj heat\$3)) with (oxygen "o.sub.2"))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	•
- :	45	((((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:20
		(silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre	US-PGPUB;	
	1	adj heat\$3)) and (oxygen "o.sub.2"))	EPO; JPO;	1
		adjinodito), dina (onjigoni olodini),	DERWENT:	1
			IBM TDB	
_	4	((((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:18
		(silicon semiconductor)) and clean\$4)) and ((preheat\$3 (pre	US-PGPUB;	
		adj heat\$3)) and (oxygen "o.sub.2"))) and @ad<=19951025	EPO; JPO;	
		adj ficatipo// and (oxygen o.sas.2 /// and was 1000 for	DERWENT:	
	Ì		IBM_TDB	
	270	((((())ocor with enectallization) and laser with anneal\$3) and	USPAT:	2003/01/03 15:20
-	2/0	(((((laser with crystallization) and laser with anneal\$3) and	US-PGPUB;	2003/01/03 13.20
		(silicon semiconductor)) and clean\$4)) and ((heat\$3) and	EPO; JPO;	
		(oxygen "o.sub.2"))		
	i		DERWENT;	
		/////	IBM_TDB	2002/04/02 45:00
-	62	(((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:20
		(silicon semiconductor)) and clean\$4)) and ((heat\$3) with	US-PGPUB;	
		(oxygen "o.sub.2"))	EPO; JPO;	
			DERWENT;	
l			IBM_TDB	
-	10	((((((laser with crystallization) and laser with anneal\$3) and	USPAT;	2003/01/03 15:21
		(silicon semiconductor)) and clean\$4)) and ((heat\$3) with	US-PGPUB;	İ
	1	(oxygen "o.sub.2"))) and @ad<=19951025	EPO; JPO;	1
,			DERWENT;	! !
	,		IBM_TDB	1
-	4493	laser with nitrogen	USPAT;	2003/01/06 10:28
		Ĭ	US-PGPUB;	
	Į l		EPO; JPO;	ı
]		DERWENT:	!
)		IBM TDB	
_	2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795)	USPAT:	2003/01/06 10:10
	2910	or (438/909) or (438/for.200) or (438/for.269) or (438/for.334)	US-PGPUB;	
	1		EPO; JPO;	
!	!	or (117/8) or (117/9) or (117/10)).CCLS.	DERWENT;	
1	!			İ
			IBM_TDB	

		,		
-	2978	((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.	USPAT; US-PGPUB; EPO; JPO;	2003/01/06 10:10
į	i		DERWENT;	
	ļ		IBM_TDB	,
•	73	or (438/509) or (438/795) or (438/909) or (438/FOR.200) or	USPAT; US-PGPUB;	2003/01/06 10:11
		(438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.)	EPO; JPO; DERWENT; IBM TDB	1
	1	((laser with nitrogen) and (((438/166) or (438/905) or (438/487)	USPAT;	2003/01/06 10:12
-	25	or (438/509) or (438/795) or (438/909) or (438/FOR.200) or (438/FOR.269) or (438/FOR.334) or (117/8) or (117/9) or (117/10)).CCLS.)) and @ad<=19951025	US-PGPUB; EPO; JPO; DERWENT;	2000/01/00 10:12
	Ì		IBM_TDB	
-	1320	(((438/166) or (438/905) or (438/487) or (438/509) or (438/795) or (438/909) or (438/for.200) or (438/for.269) or (438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and	USPAT; US-PGPUB; EPO; JPO;	2003/01/06 10:32
		crystal\$ with silicon	DERWENT;	
	947	! ` ((((438/166) or (438/905) or (438/487) or (438/509) or	IBM_TDB USPAT:	2003/01/06 11:46
-		(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	2000/01/00 11:10
	i	(438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and	EPO; JPO; DERWENT;	
		crystal\$ with silicon) and laser	IBM TDB	1
-	258	(((((438/166) or (438/905) or (438/487) or (438/509) or	USPAT:	2003/01/07 11:18
	200	(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	1
		(438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and	EPO; JPO;	
		crystal\$ with silicon) and laser) and anneal	DERWENT;	
	29	((((438/166) or (438/905) or (438/487) or (438/509) or	IBM_TDB USPAT;	2003/01/06 10:47
		(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	†
	}	(438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and	EPO; JPO;	
		crystal\$ with silicon) and oxidation with nitrogen	DERWENT; IBM TDB	
-	14		USPAT;	2003/01/06 11:45
		(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	
		(438/for 334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and oxidation with nitrogen) and	EPO; JPO; DERWENT;	
		@ad<=19951025	IBM TDB	
-	48	((((438/166) or (438/905) or (438/487) or (438/509) or	USPAT;	2003/01/06 11:47
	ŀ	(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	1
		(438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and laser with air	: EPO; JPO; ; DERWENT;	
		Crystala with silicon) and laser with all	IBM TDB	
_	18		USPAT;	2003/01/06 11:47
		(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	1
		(438/for.334) or (117/8) or (117/9) or (117/10)) CCLS.) and	EPO; JPO; DERWENT;	1
		crystal\$ with silicon) and laser with air) and @ad<=19951025	IBM TDB	}
-	118	(laser with crystallization) and laser with air	USPAT;	2003/01/07 11:18
			US-PGPUB;	
	-		EPO; JPO; DERWENT;	•
			IBM TDB	1
-	16		USPAT;	2003/01/07 11:19
		(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	
		(438/for 334) or (117/8) or (117/9) or (117/10)).CCLS.) and crystal\$ with silicon) and (laser with air)) and anneal	EPO; JPO; DERWENT;	! [
		Crystale with Silicon) and (laser with all)) and annear	IBM TOB	
	4	((((((438/166) or (438/905) or (438/487) or (438/509) or	USPAT;	2003/01/07 11:19
		(438/795) or (438/909) or (438/for.200) or (438/for.269) or	US-PGPUB;	
		(438/for.334) or (117/8) or (117/9) or (117/10)).CCLS.) and	EPO; JPO;	l .
		crystal\$ with silicon) and (laser with air)) and anneal) and	DERWENT,	
		@ad<=19951025	IBM_TDB	